

DATA SHEET

PDTC123E series
NPN resistor-equipped transistors;
 $R1 = 2.2 \text{ k}\Omega$, $R2 = 2.2 \text{ k}\Omega$

Product specification
Supersedes data of 2004 Mar 18

2004 Aug 06

**NPN resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ**

PDTC123E series

FEATURES

- Built-in bias resistors
- Simplified circuit design
- Reduction of component count
- Reduced pick and place costs.

APPLICATIONS

- General purpose switching and amplification
- Inverter and interface circuits
- Circuit driver.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	TYP.	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–	50	V
I_o	output current (DC)	–	100	mA
R1	bias resistor	2.2	–	kΩ
R2	bias resistor	2.2	–	kΩ

DESCRIPTION

NPN resistor-equipped transistor (see “Simplified outline, symbol and pinning” for package details).

PRODUCT OVERVIEW

TYPE NUMBER	PACKAGE		MARKING CODE	PNP COMPLEMENT
	PHILIPS	EIAJ		
PDTC123EE	SOT416	SC-75	5A	PDTA123EE
PDTC123EEF	SOT490	SC-89	6A	PDTA123EEF
PDTC123EK	SOT346	SC-59	48	PDTA123EK
PDTC123EM	SOT883	SC-101	G1	PDTA123EM
PDTC123ES	SOT54 (TO-92)	SC-43	TC123E	PDTA123ES
PDTC123ET	SOT23	–	*26 ⁽¹⁾	PDTA123ET
PDTC123EU	SOT323	SC-70	*48 ⁽¹⁾	PDTA123EU

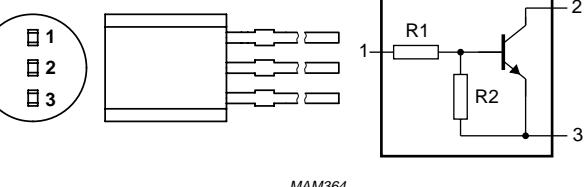
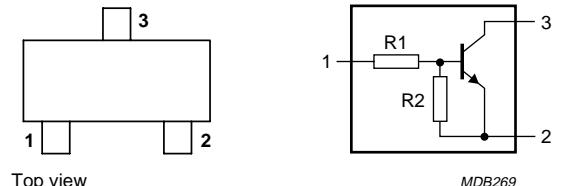
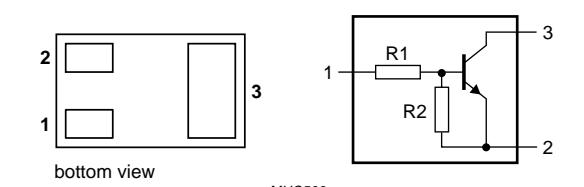
Note

1. * = p: Made in Hong Kong.
- * = t: Made in Malaysia.
- * = W: Made in China.

NPN resistor-equipped transistors;
R1 = 2.2 k Ω , R2 = 2.2 k Ω

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SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL	PINNING	
		PIN	DESCRIPTION
PDTC123ES	 <p>MAM364</p>	1 2 3	base collector emitter
PDTC123EE PDTC123EEF PDTC123EK PDTC123ET PDTC123EU	 <p>Top view</p> <p>MDB269</p>	1 2 3	base emitter collector
PDTC123EM	 <p>bottom view</p> <p>MHC506</p>	1 2 3	base emitter collector

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PDTC123E series

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PDTC123EE	–	plastic surface mounted package; 3 leads	SOT416
PDTC123EEF	–	plastic surface mounted package; 3 leads	SOT490
PDTC123EK	–	plastic surface mounted package; 3 leads	SOT346
PDTC123EM	–	leadless ultra small package; 3 solder lands; body 1.0 × 0.6 × 0.5 mm	SOT883
PDTC123ES	–	plastic single-ended leaded (through hole) package; 3 leads	SOT54
PDTC123ET	–	plastic surface mounted package; 3 leads	SOT23
PDTC123EU	–	plastic surface mounted package; 3 leads	SOT323

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	50	V
V_{CEO}	collector-emitter voltage	open base	–	50	V
V_{EBO}	emitter-base voltage	open collector	–	10	V
V_I	input voltage positive negative		–	+12	V
–			–	–10	V
I_O	output current (DC)		–	100	mA
I_{CM}	peak collector current		–	100	mA
P_{tot}	total power dissipation SOT54 SOT23 SOT346 SOT323 SOT416 SOT490 SOT883	$T_{amb} \leq 25^\circ\text{C}$ note 1 note 1 note 1 note 1 note 1 notes 1 and 2 notes 2 and 3	– – – – – – – –	500 250 250 200 150 250 250	mW mW mW mW mW mW mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C
T_{amb}	operating ambient temperature		–65	+150	°C

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

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THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air		
		note 1	250	K/W
		note 1	500	K/W
		note 1	500	K/W
		note 1	625	K/W
		note 1	833	K/W
		notes 1 and 2	500	K/W
		notes 2 and 3	500	K/W

Notes

1. Refer to standard mounting conditions.
2. Reflow soldering is the only recommended soldering method.
3. Refer to SOT883 standard mounting conditions; FR4 with 60 µm copper strip line.

CHARACTERISTICS

T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 50$ V; $I_E = 0$ A	–	–	100	nA
I_{CEO}	collector-emitter cut-off current	$V_{CE} = 30$ V; $I_B = 0$ A	–	–	1	µA
		$V_{CE} = 30$ V; $I_B = 0$ A; $T_j = 150$ °C	–	–	50	µA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5$ V; $I_C = 0$ A	–	–	2	mA
h_{FE}	DC current gain	$V_{CE} = 5$ V; $I_C = 20$ mA	30	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10$ mA; $I_B = 0.5$ mA	–	–	150	mV
$V_{i(off)}$	input-off voltage	$I_C = 1$ mA; $V_{CE} = 5$ V	–	1.2	0.5	V
$V_{i(on)}$	input-on voltage	$I_C = 20$ mA; $V_{CE} = 0.3$ V	2	1.6	–	V
$R1$	input resistor		1.54	2.2	2.86	kΩ
$\frac{R2}{R1}$	resistor ratio		0.8	1	1.2	
C_c	collector capacitance	$V_{CB} = 10$ V; $I_E = i_e = 0$ A; $f = 1$ MHz	–	–	2.5	pF

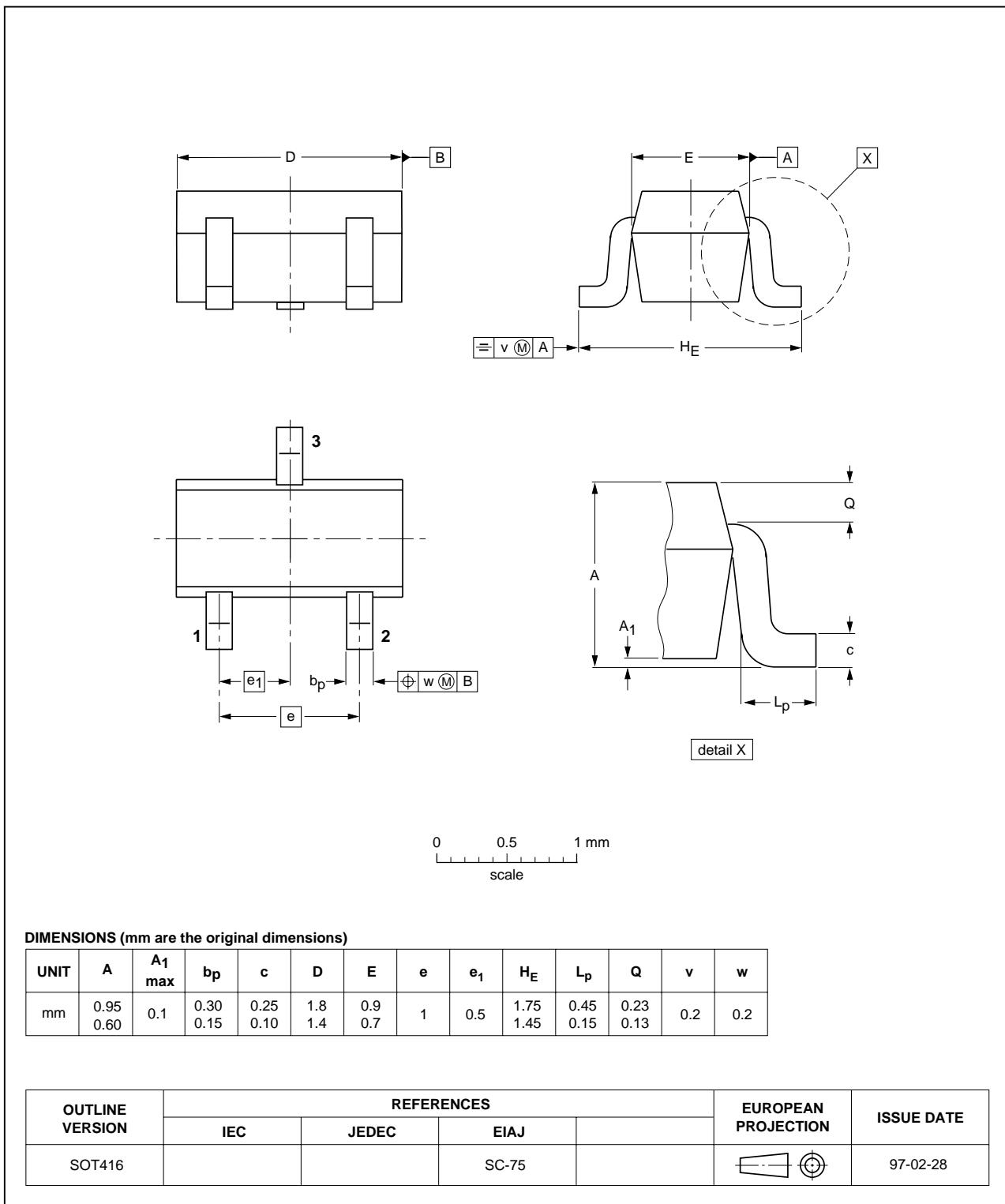
NPN resistor-equipped transistors;
 R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTC123E series

PACKAGE OUTLINES

Plastic surface mounted package; 3 leads

SOT416

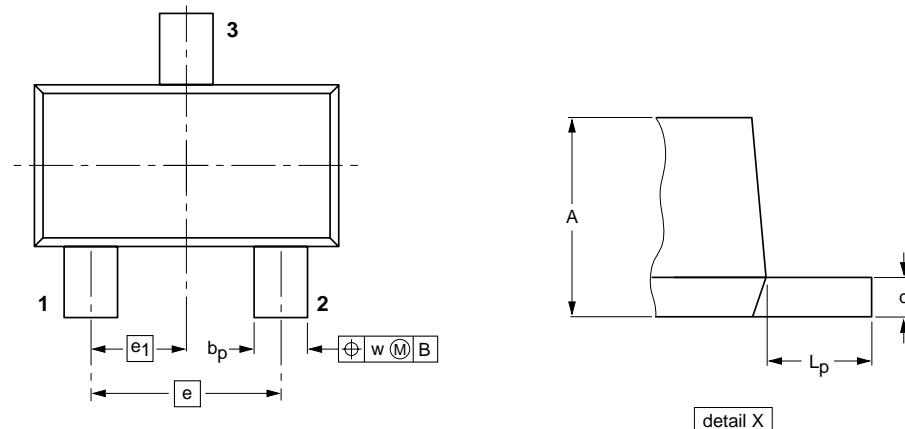
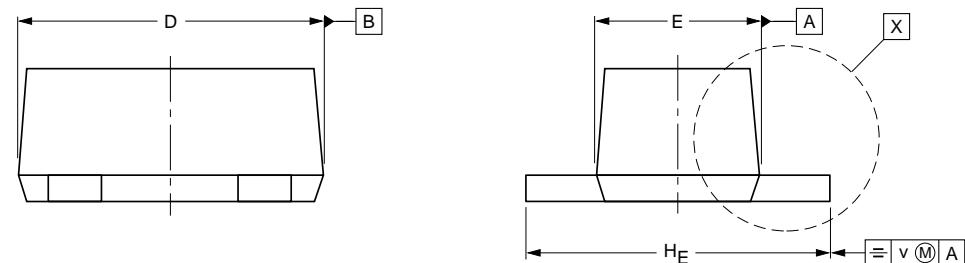


NPN resistor-equipped transistors;
 R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTC123E series

Plastic surface mounted package; 3 leads

SOT490



0 1 2 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b_p	c	D	E	e	e_1	H_E	L_p	v	w
mm	0.8 0.6	0.33 0.23	0.2 0.1	1.7 1.5	0.95 0.75	1.0	0.5	1.7 1.5	0.5 0.3	0.1	0.1

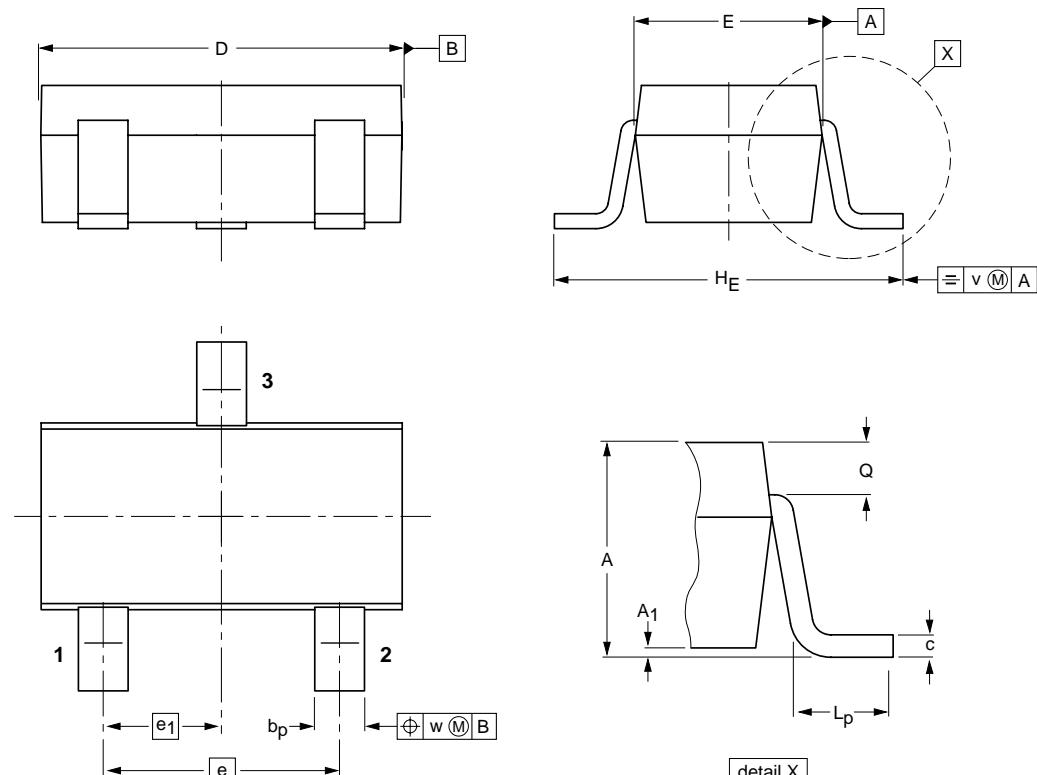
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ	SC-89		
SOT490						98-10-23

NPN resistor-equipped transistors;
R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTC123E series

Plastic surface mounted package; 3 leads

SOT346



0 1 2 mm
scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b_p	c	D	E	e	e_1	H_E	l_p	Q	v	w
mm	1.3 1.0	0.013	0.50 0.35	0.26 0.10	3.1 2.7	1.7 1.3	1.9	0.95	3.0 2.5	0.6 0.2	0.33 0.23	0.2	0.2

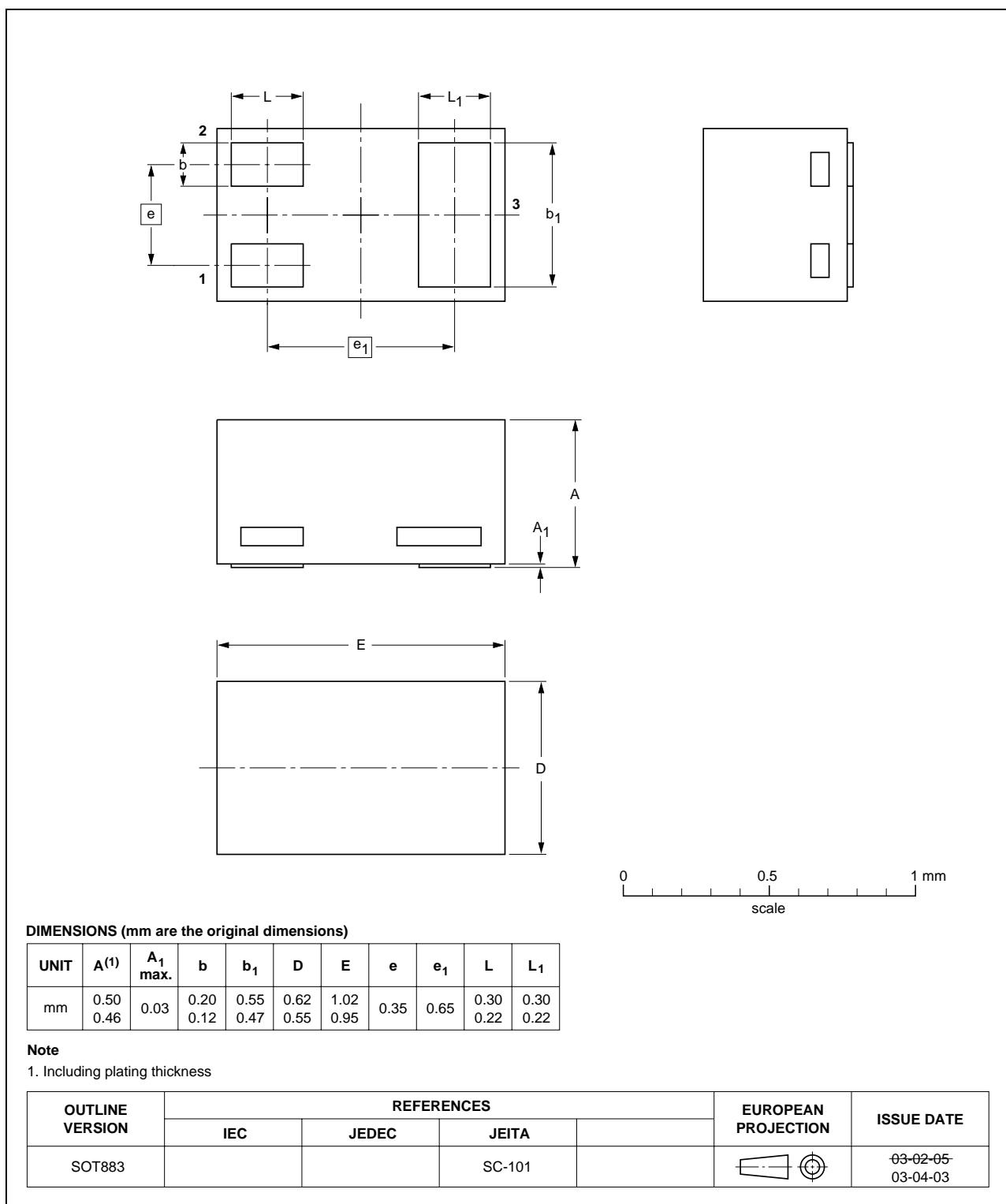
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT346		TO-236	SC-59			98-07-17

NPN resistor-equipped transistors;
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Leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.5 mm

SOT883

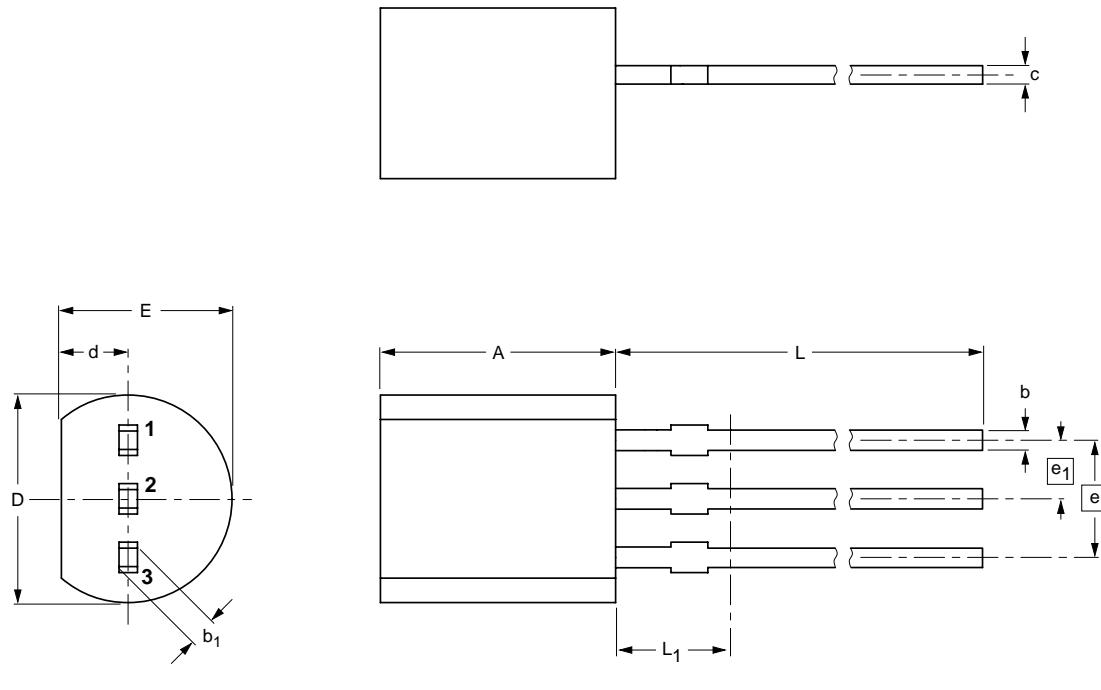


NPN resistor-equipped transistors;
 R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTC123E series

Plastic single-ended leaded (through hole) package; 3 leads

SOT54



0 2.5 5 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	b	b ₁	c	D	d	E	e	e ₁	L	L ₁ ⁽¹⁾ max.
mm	5.2 5.0	0.48 0.40	0.66 0.55	0.45 0.38	4.8 4.4	1.7 1.4	4.2 3.6	2.54	1.27	14.5 12.7	2.5

Note

1. Terminal dimensions within this zone are uncontrolled to allow for flow of plastic and terminal irregularities.

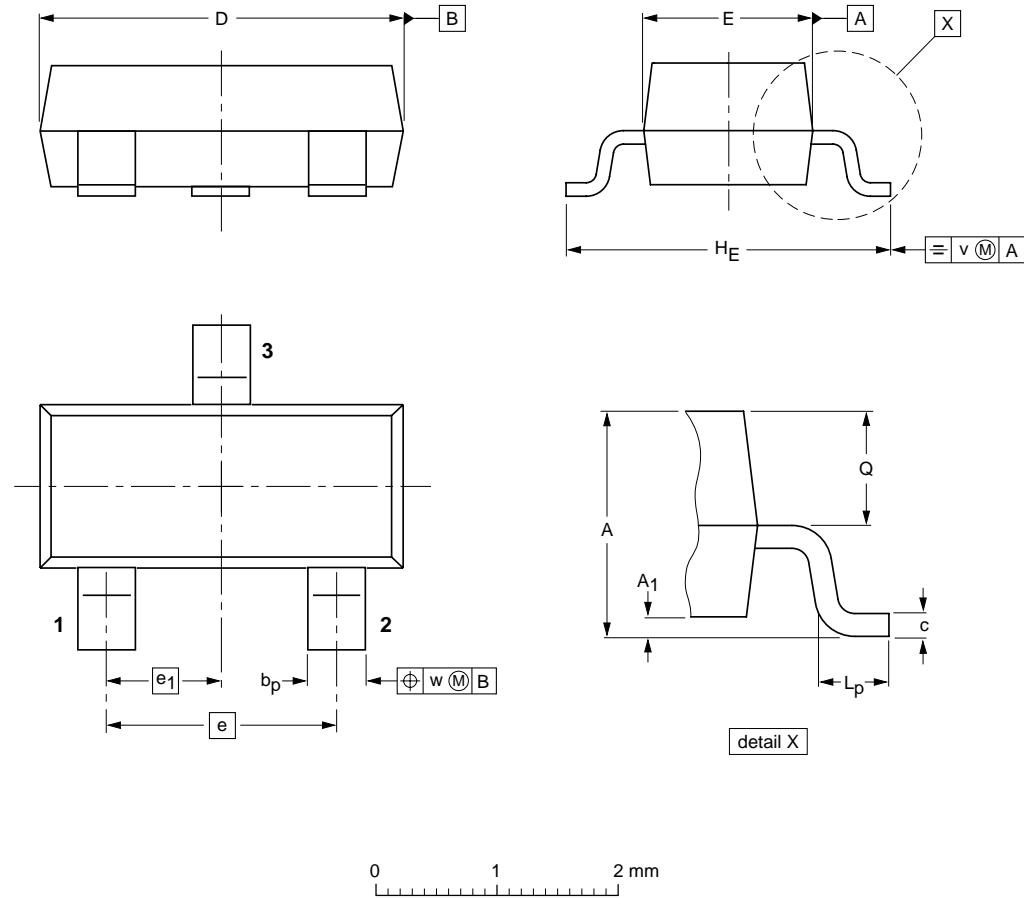
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT54		TO-92	SC-43A			-97-02-28 04-06-28

NPN resistor-equipped transistors;
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PDTC123E series

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

DIMENSIONS (mm are the original dimensions)													
UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

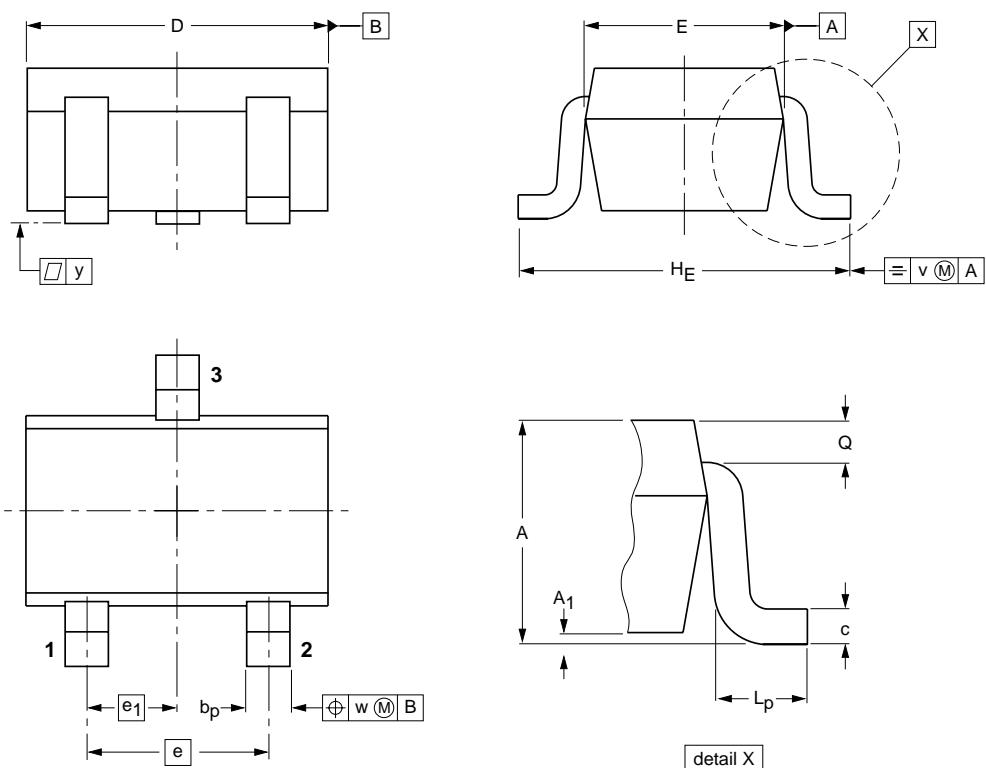
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SOT23		TO-236AB				-97-02-28 99-09-13

NPN resistor-equipped transistors;
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Plastic surface mounted package; 3 leads

SOT323



0 1 2 mm
 scale

DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.8	0.1	0.4 0.3	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.23 0.13	0.2	0.2

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT323			SC-70			97-02-28

NPN resistor-equipped transistors;
 R1 = 2.2 kΩ, R2 = 2.2 kΩ

PDTC123E series

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
II	Preliminary data	Qualification	This data sheet contains data from the preliminary specification. Supplementary data will be published at a later date. Philips Semiconductors reserves the right to change the specification without notice, in order to improve the design and supply the best possible product.
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Notes

1. Please consult the most recently issued data sheet before initiating or completing a design.
2. The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.
3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

DEFINITIONS

Short-form specification — The data in a short-form specification is extracted from a full data sheet with the same type number and title. For detailed information see the relevant data sheet or data handbook.

Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device.

These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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